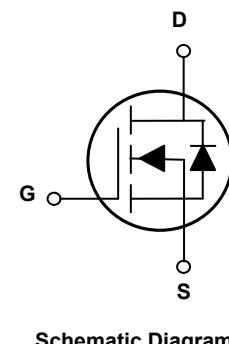
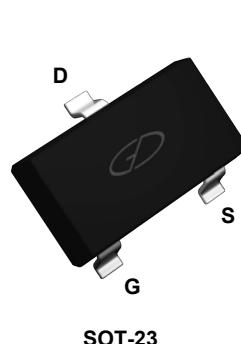


## Main Product Characteristics

$V_{(BR)DSS}$	20V
$R_{DS(ON)}$	44mΩ (max.)
$I_D$	4A



## Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



## Description

The SSF2302 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 10$	V
Continuous Drain Current, @ Steady-State @ $T_A=25^\circ\text{C}^1$	$I_D$	4	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	14	A
Power Dissipation	$P_D$	1	W
Junction-to-Ambient (PCB Mounted, Steady-State)	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Storage Temperature Range	$T_{STG}$	-55 To +150	$^\circ\text{C}$
Operating Junction Temperature Range	$T_J$	-55 To +150	$^\circ\text{C}$

**Electrical Characteristics** ( $T_A=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>On / Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	20	-	-	V
$\text{BV}_{\text{DSS}}$ Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	Reference to $25^\circ\text{C}$ , $I_{\text{D}}=1\text{mA}$	-	0.02	-	$\text{V}/^\circ\text{C}$
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}, T_J=25^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$V_{\text{DS}}=16\text{V}, V_{\text{GS}}=0\text{V}, T_J=125^\circ\text{C}$	-	-	10	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 10\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	$\text{nA}$
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=3\text{A}$	-	27	44	$\text{m}\Omega$
		$V_{\text{GS}}=2.5\text{V}, I_{\text{D}}=2\text{A}$	-	35	58	
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}, I_{\text{D}}=250\mu\text{A}$	0.3	0.6	1	V
$V_{\text{GS}(\text{th})}$ Temperature Coefficient	$\Delta V_{\text{GS}(\text{th})}$		-	-2	-	$\text{mV}/^\circ\text{C}$
Forward Transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=2\text{A}$	-	4.4	-	S
<b>Dynamic and Switching Characteristics</b>						
Total Gate Charge <sup>2,3</sup>	$Q_g$	$V_{\text{DS}}=10\text{V}, V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=3\text{A}$	-	5.8	-	$\text{nC}$
Gate-Source Charge <sup>2,3</sup>	$Q_{\text{gs}}$		-	0.6	-	
Gate-Drain Charge <sup>2,3</sup>	$Q_{\text{gd}}$		-	1.5	-	
Turn-On Delay Time <sup>2,3</sup>	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=10\text{V}, V_{\text{GS}}=4.5\text{V}, R_{\text{G}}=25\Omega, I_{\text{D}}=1\text{A}$	-	2.9	-	$\text{nS}$
Rise Time <sup>2,3</sup>	$t_r$		-	8.4	-	
Turn-Off Delay Time <sup>2,3</sup>	$t_{\text{d}(\text{off})}$		-	19.2	-	
Fall Time <sup>2,3</sup>	$t_f$		-	5.6	-	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, F=1\text{MHz}$	-	314	-	$\text{pF}$
Output Capacitance	$C_{\text{oss}}$		-	50	-	
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	40	-	
<b>Source-Drain Ratings and Characteristics</b>						
Continuous Source Current	$I_s$	$V_G=V_D=0\text{V}$ , Force Current	-	-	4.0	A
Pulsed Source Current	$I_{\text{SM}}$		-	-	14	A
Diode Forward Voltage	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_s=1\text{A}, T_J=25^\circ\text{C}$	-	-	1	V

Notes:

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
3. Essentially independent of operating temperature.

## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise specified)

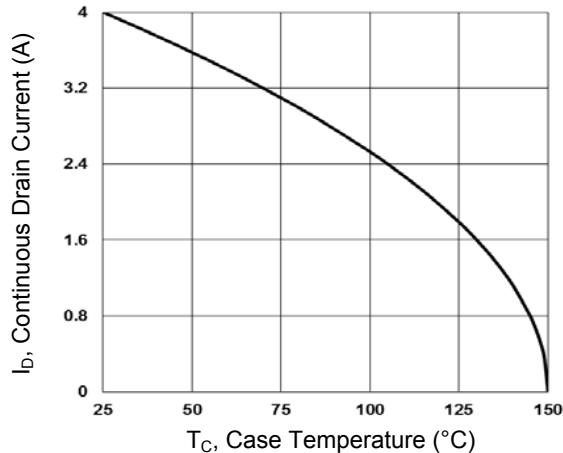


Figure 1. Continuous Drain Current vs.  $T_c$

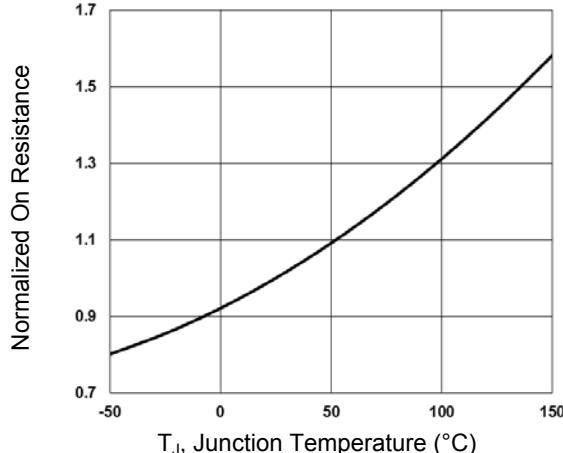


Figure 2. Normalized  $R_{DS(ON)}$  vs.  $T_j$

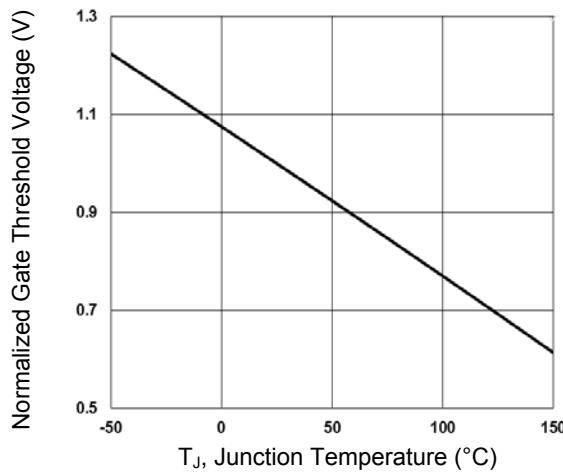


Figure 3. Normalized  $V_{th}$  vs.  $T_j$

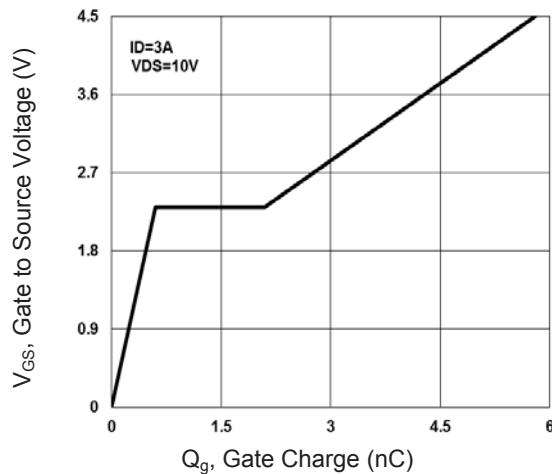


Figure 4. Gate Charge Waveform

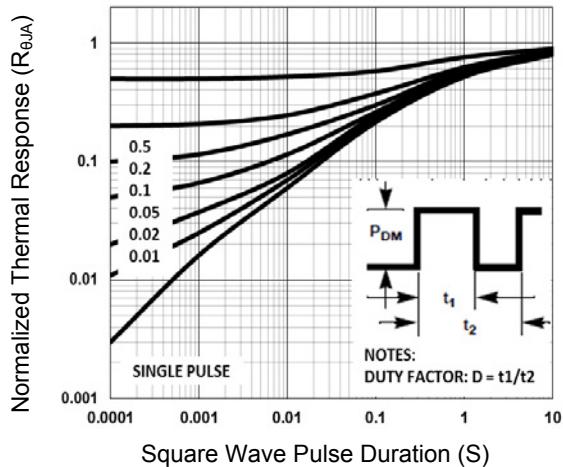


Figure 5. Normalized Transient Impedance

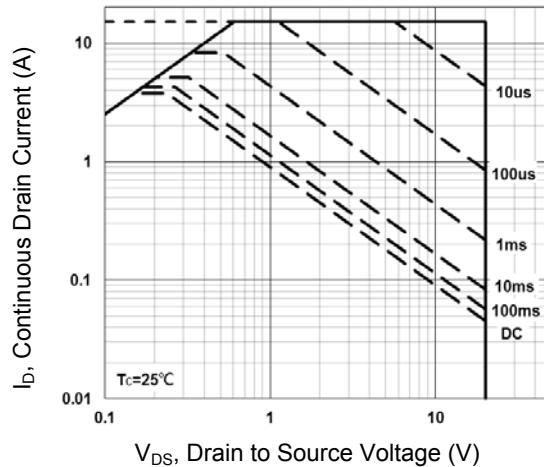
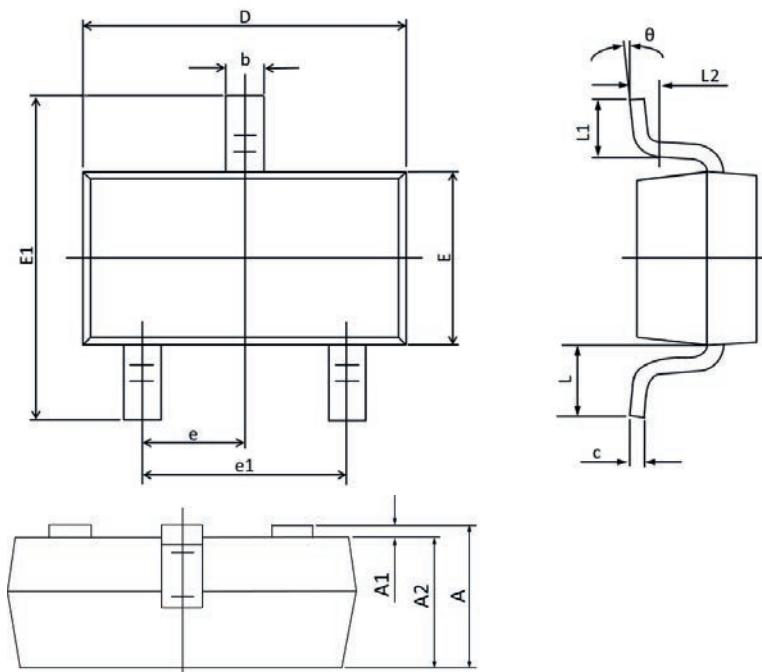


Figure 6. Maximum Safe Operation Area

### Package Outline Dimensions (SOT-23)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.250	1.840	0.049	0.072
E1	2.250	2.550	0.089	0.100
e	0.95 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.55 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
L2	0.25 TYP.		0.01 TYP.	
θ	0°	8°	0°	8°

### Order Information

Device	Package	Marking	Carrier	Quantity
SSF2302	SOT-23	2302	Tape & Reel	3,000 pcs / Reel

For more information, please contact us at: [inquiry@goodarksemi.com](mailto:inquiry@goodarksemi.com)